



**KTH Informations- och
kommunikationsteknik**

IE1204 Digital Design:

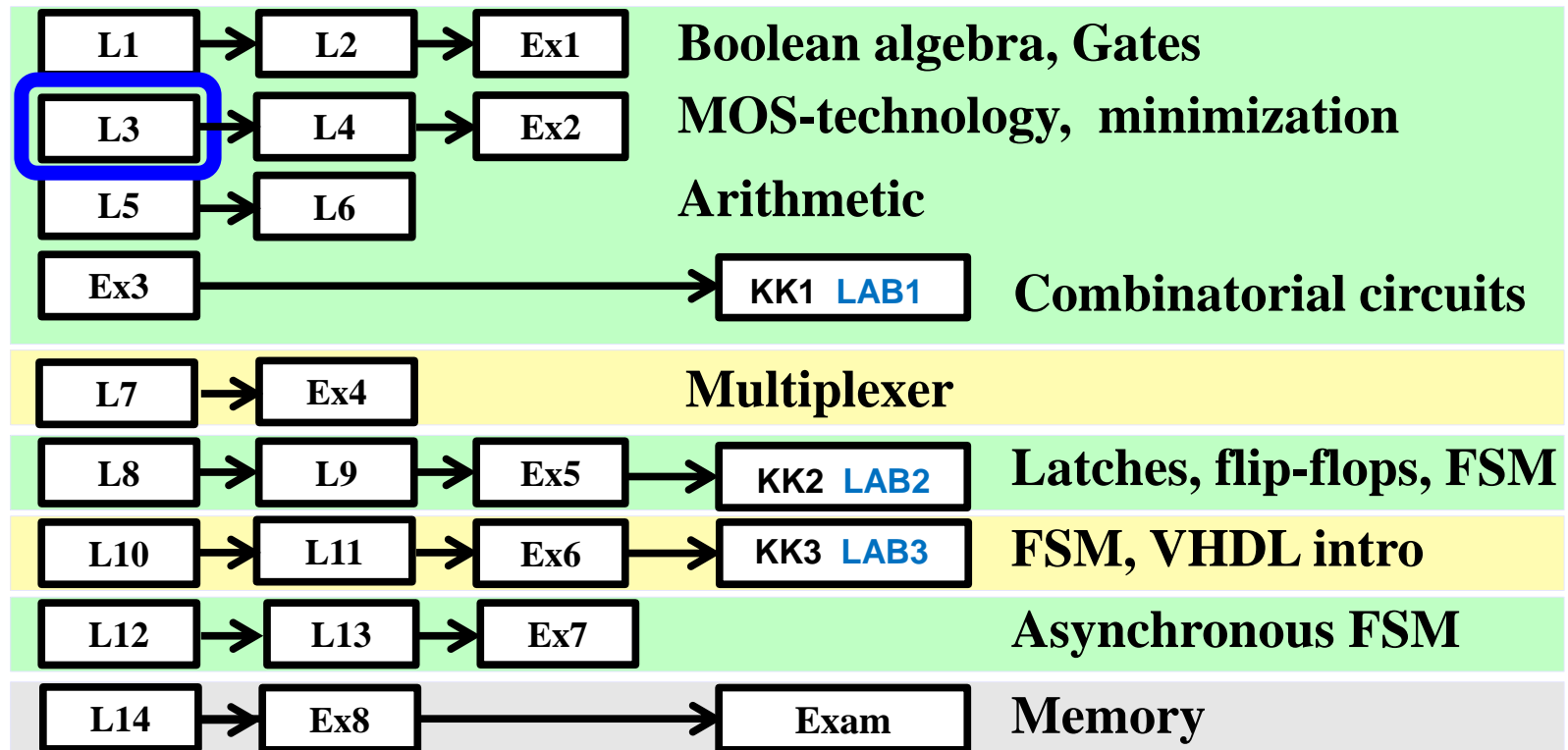
L3: CMOS circuits, Implementation Technologies

Masoumeh (Azin) Ebrahimi

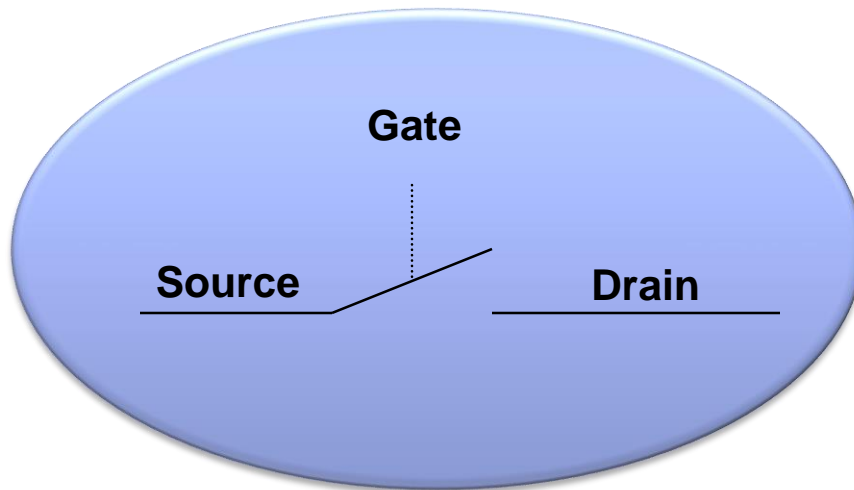
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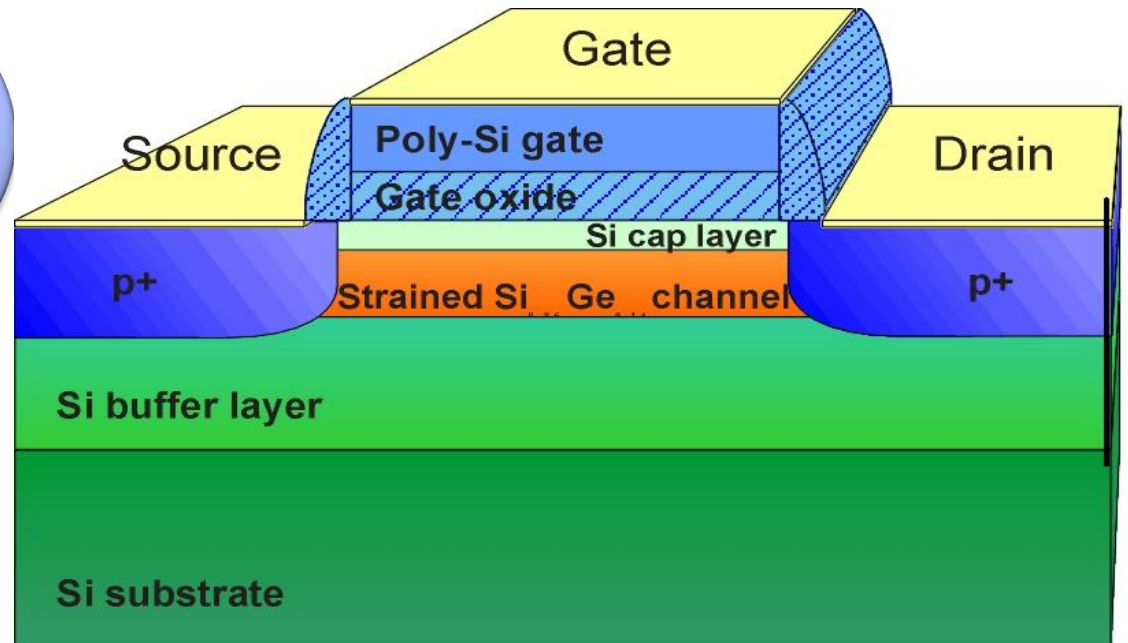
IE1204 Digital Design



Transistor - a switch with no moving parts



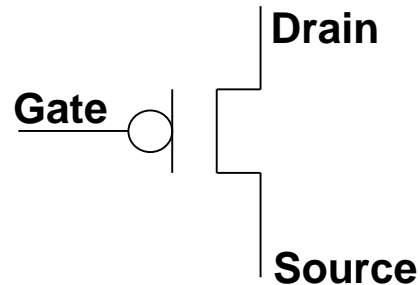
Schematic diagram of
the SiGe transistor
(KTH)



Why CMOS?

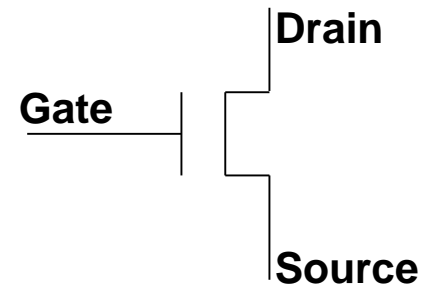
- CMOS transistors are easy to manufacture
- CMOS transistors are made from ordinary sand
=> cheap raw materials
- A transistor is easy to get to work as a switch

PMOS and NMOS transistors



PMOS

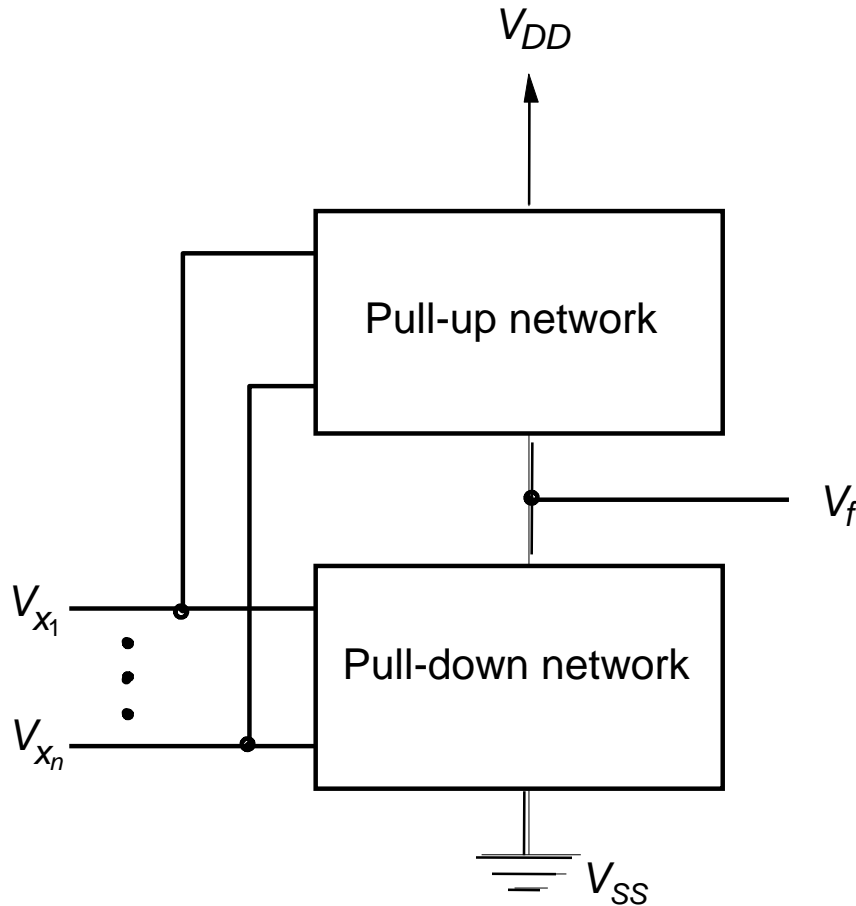
A PMOS transistor (p-channel MOS) is conducting (switch is closed) if the gate voltage (V_{GS}) is close to V_{SS} .



NMOS

An NMOS (n-channel) is conducting (switch is closed) if the gate voltage (V_{GS}) is close to V_{DD} .

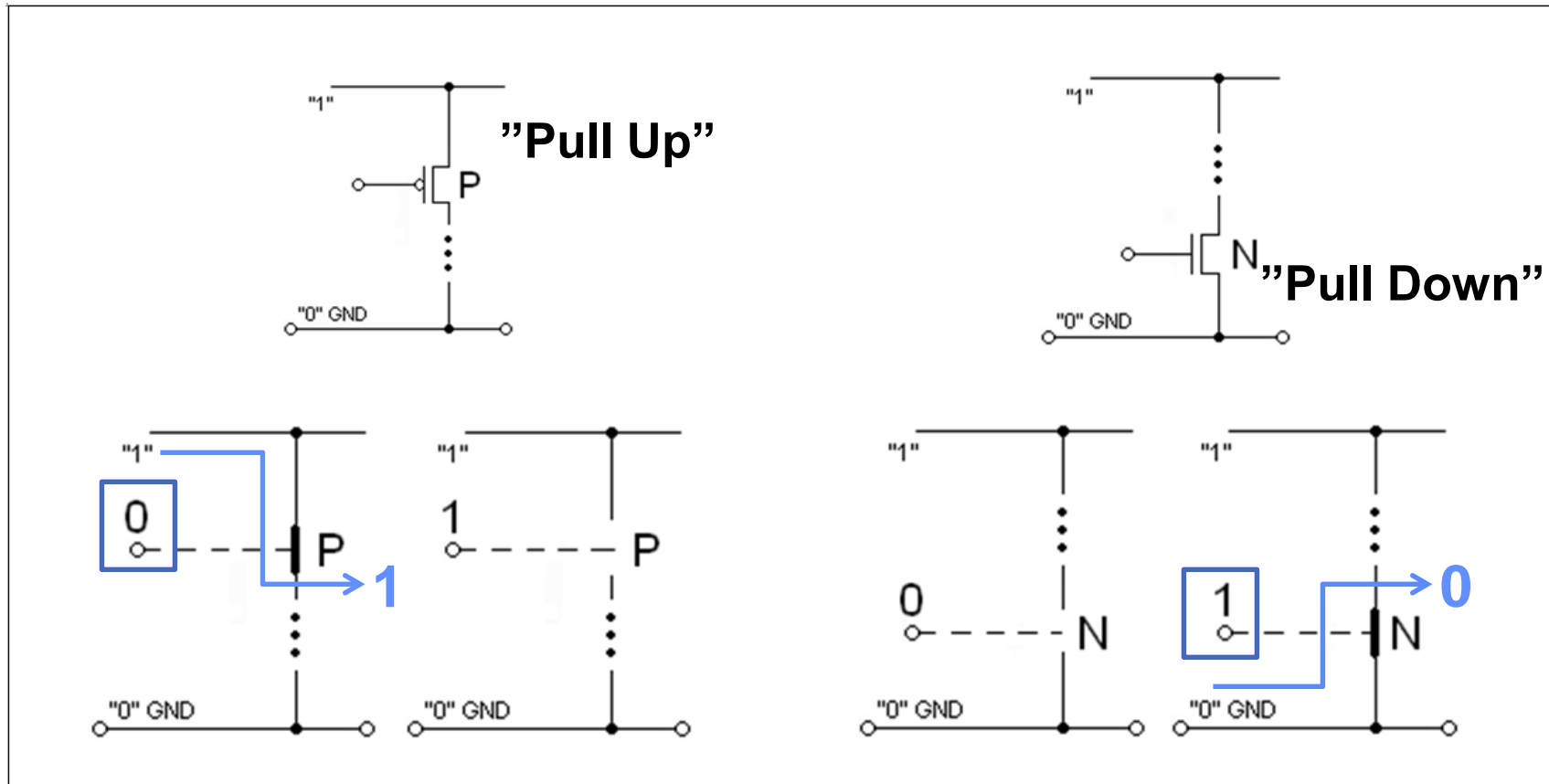
The structure of a CMOS circuit



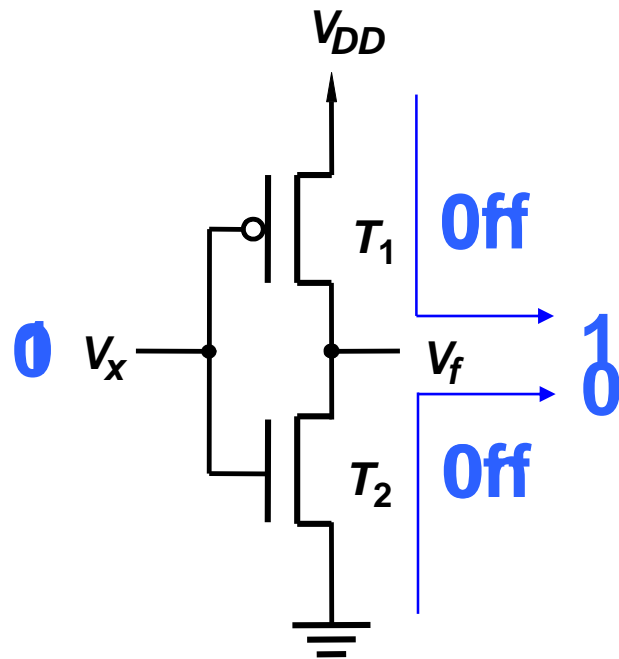
PMOS makes the output "1"

NMOS makes the output "0"

PMOS and NMOS Transistors



CMOS inverter



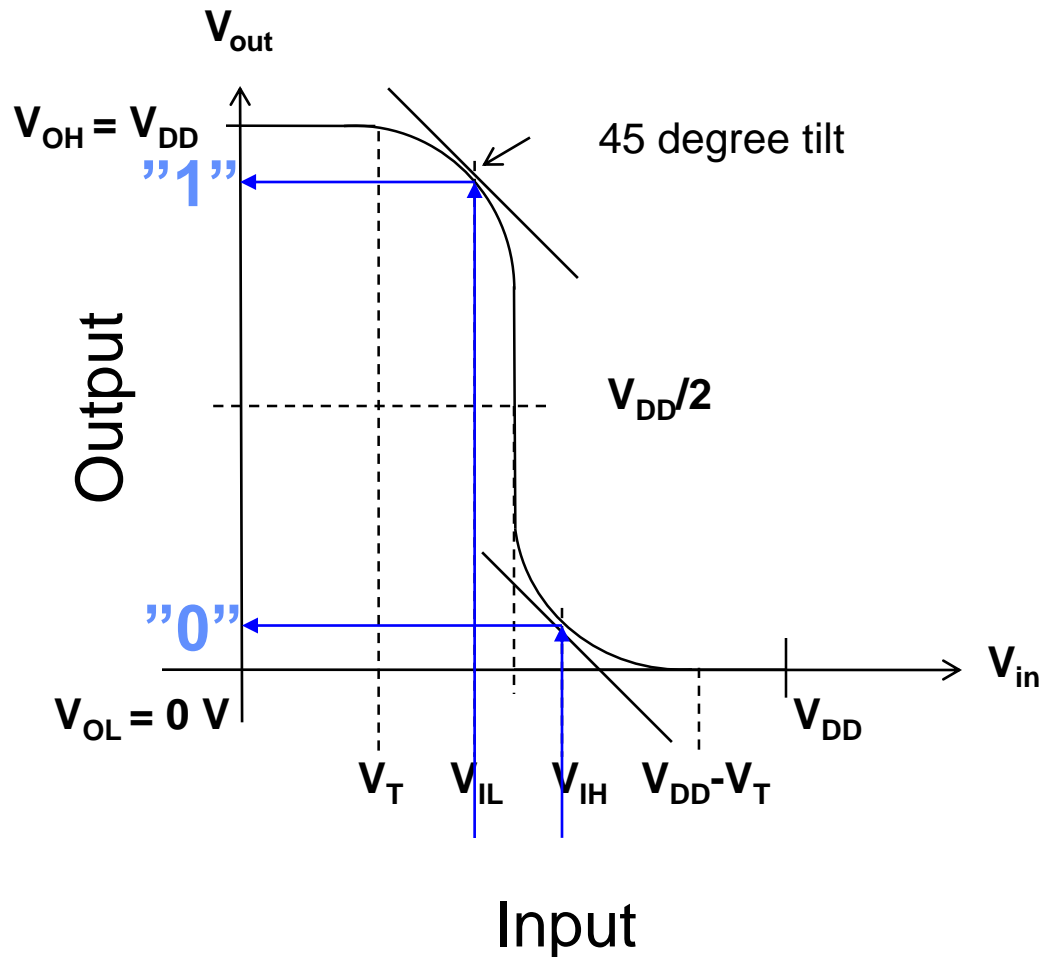
(A) Circuit

- CMOS circuits are composed of both PMOS and NMOS transistors
- CMOS stands for Complementary MOS
- Area: $A_{\text{Inverter}} = 2 \text{ Transistors}$

x	T_1	T_2	f
0	on	off	1
1	off	on	0

(B) Truth table and transistor states

CMOS inverter voltage transfer characteristic

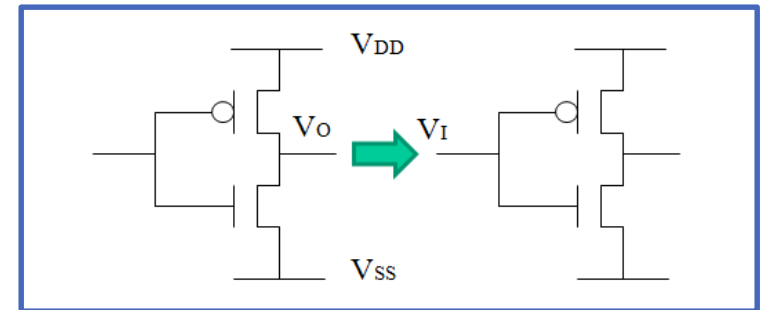


Power Supply	5.0V	3.3V	1.8V
V_{OH}	5.0	3.3	1,8
V_{IH}	2,9	1,9	1.0
V_{IL}	2,1	1,4	0.8
V_{OL}	0.0	0.0	0.0

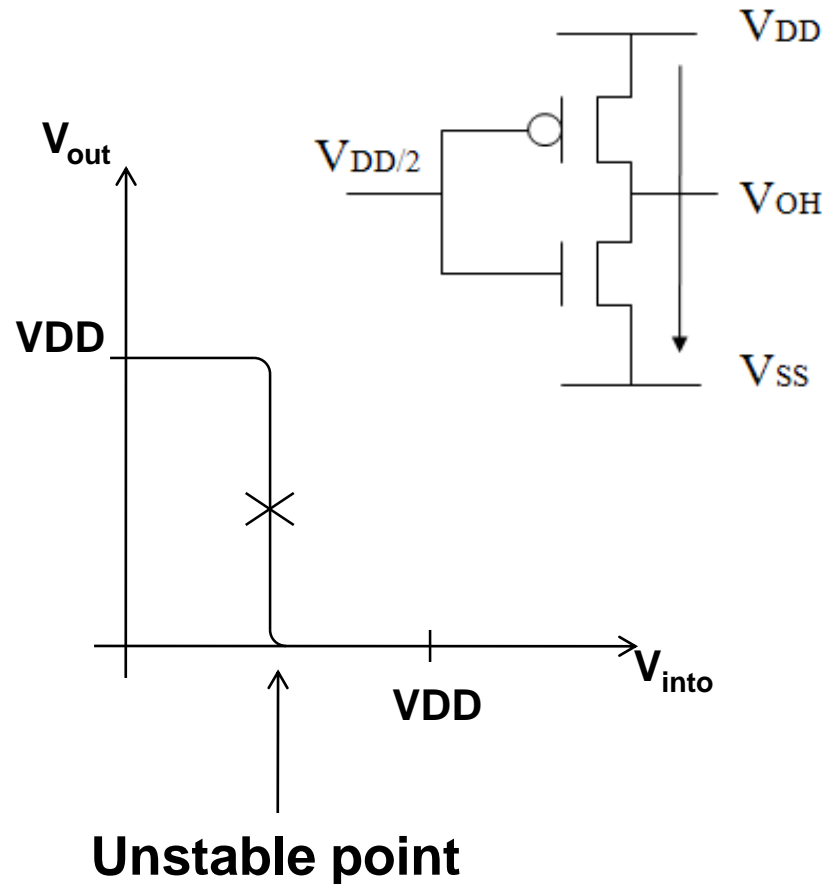
$$V_T = 0.2V_{DD}$$

$$\text{Low Noise Margin: } NM_L = V_{IL} - V_{OL}$$

$$\text{High Noise Margin } NM_H = V_{OH} - V_{IH}$$



One point is unstable!



- CMOS circuit has a very stable transfer function
- At $V_{in0} = V_{DD}/2$ there is an unstable point, then both T_1 and T_2 are conducting
- If a circuit temporarily stuck in this mode, it enters a state called *metastability*
- If this state lasts for a long time, the transistors in the circuit may be damaged by the high current

Metastability will be discussed in later lectures

Power consumption of CMOS

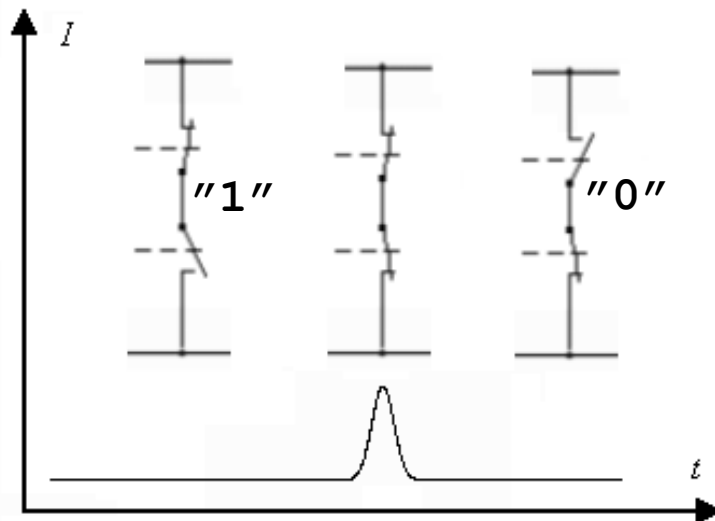
- NMOS and PMOS circuits consume both static and dynamic power
 - **Static power** is dissipated by the current that flows in the steady state
 - **Dynamic power** is dissipated when the current flows because of changes in the signal level

CMOS–Dynamic power consumption!

Classical CMOS has *only* losses exactly at the *switching point*. The Power dissipation P_F is proportional to the clock-frequency!

"1" → "0"

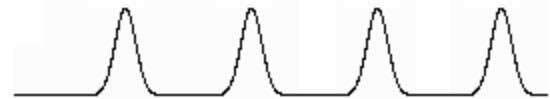
"1" ← "0"



f_C



$2 \cdot f_C$



$$P_F \propto f_C \cdot V_{DD}^2$$

P_F Power losses

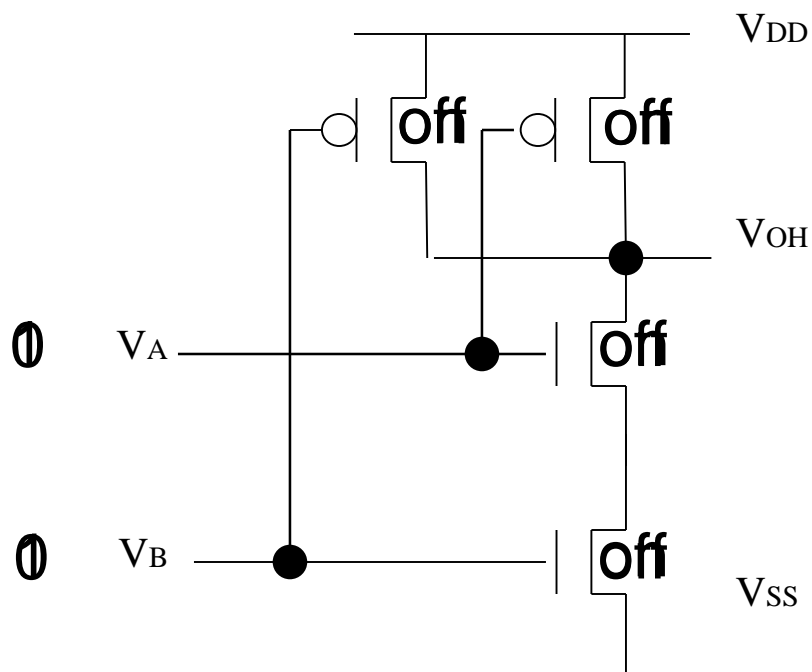
f_C Clockfrequency

V_{DD} Supply Voltage

What would the world be without the CMOS?!



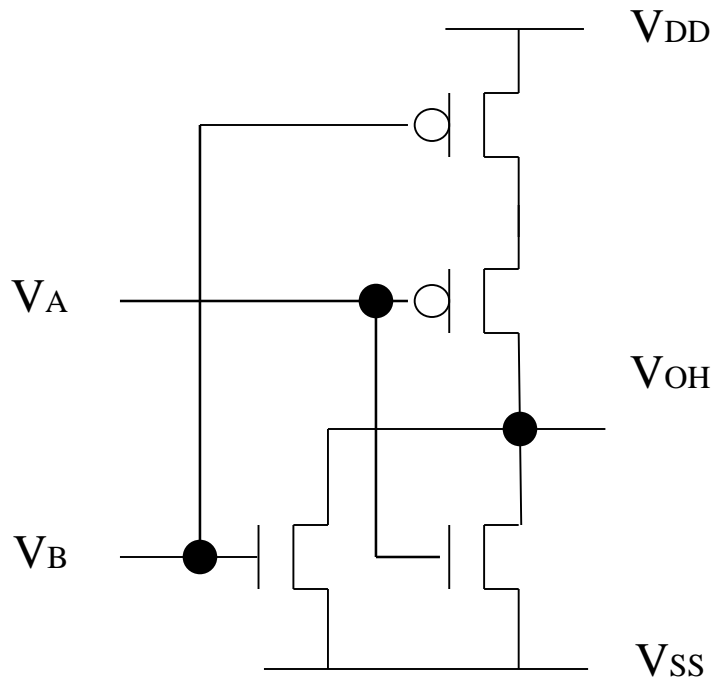
NAND gate



V_A	V_B	V_{OH}
$V_{SS}(0)$	$V_{SS}(0)$	$V_{DD}(1)$
$V_{SS}(0)$	$V_{DD}(1)$	$V_{DD}(1)$
$V_{DD}(1)$	$V_{SS}(0)$	$V_{DD}(1)$
$V_{DD}(1)$	$V_{DD}(1)$	$V_{SS}(0)$

Area: $A_{NAND} = 4$ Transistors

NOR gate



V_A	V_B	V_{OH}
$V_{SS}(0)$	$V_{SS}(0)$	$V_{DD}(1)$
$V_{SS}(0)$	$V_{DD}(1)$	$V_{SS}(0)$
$V_{DD}(1)$	$V_{SS}(0)$	$V_{SS}(0)$
$V_{DD}(1)$	$V_{DD}(1)$	$V_{SS}(0)$

Area: $A_{NOR} = 4$ Transistors

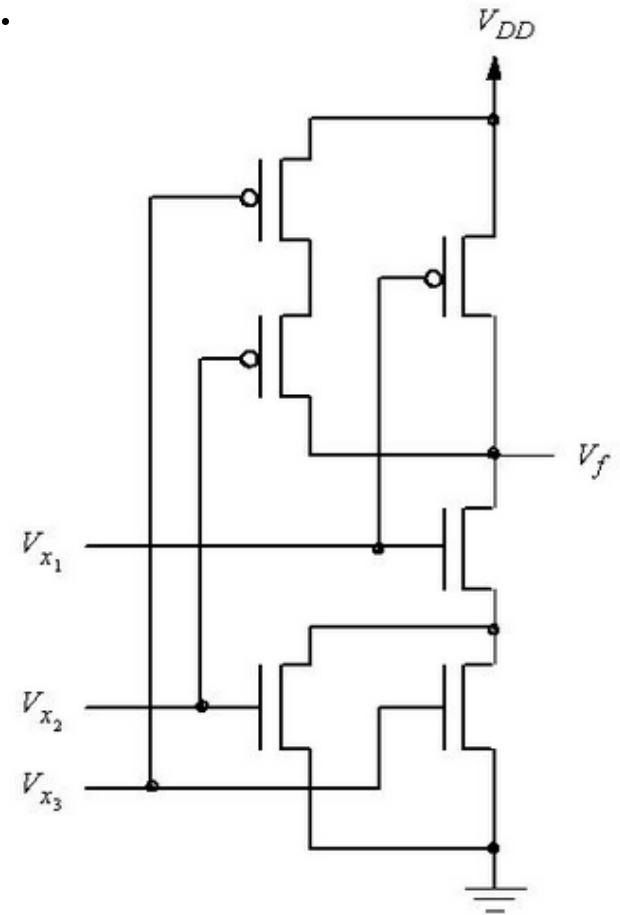
Group work



Extract the function of the following circuit.

PUN network: $F = \bar{X}_1 + \bar{X}_2 \bar{X}_3$

PDN network: $\bar{F} = X_1(X_2 + X_3) = \overline{\bar{X}_1 + \bar{X}_2 \bar{X}_3}$



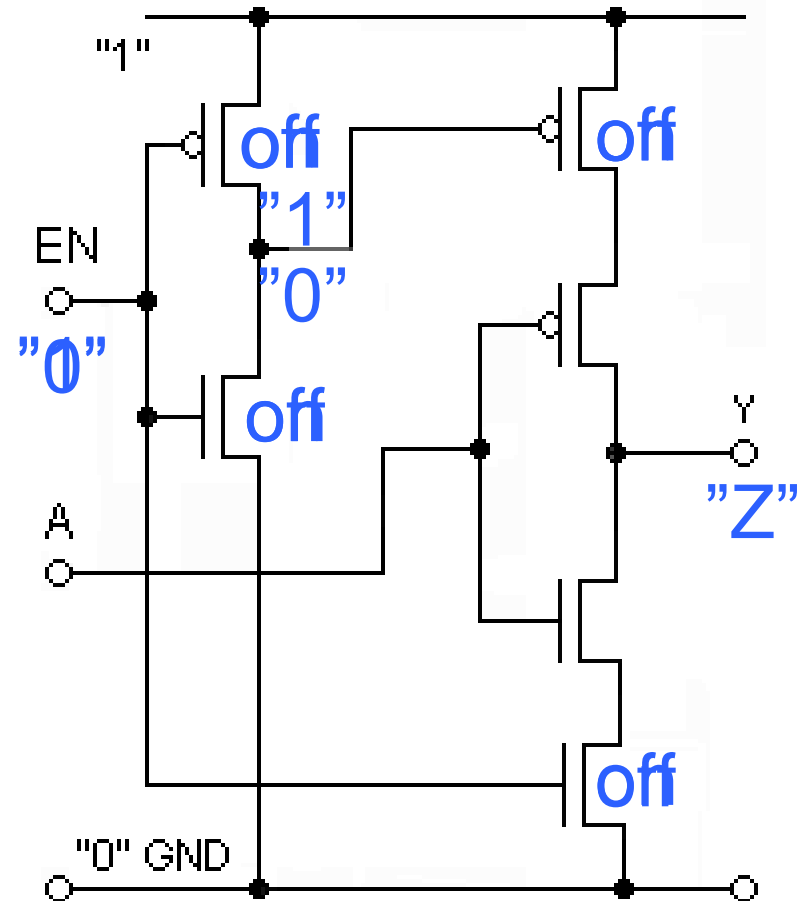
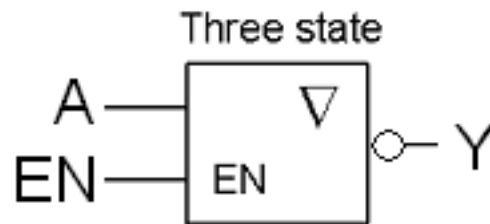
Negative logic

- You can also reverse the logic and let L (low voltage) represent the logic 1 and H (high voltage) represent the logic 0
 - This is called *negative logic*
 - An AND function becomes an OR function and vice versa
 - It is not important which logic is used - negative or positive, but positive logic is more traditional
-

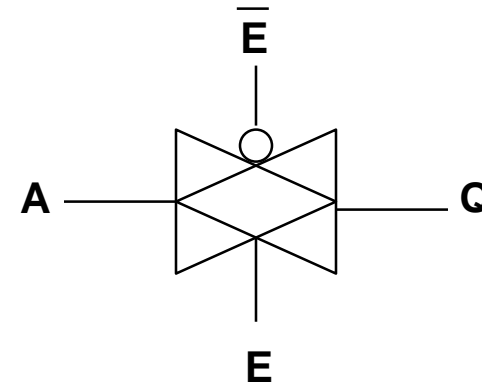
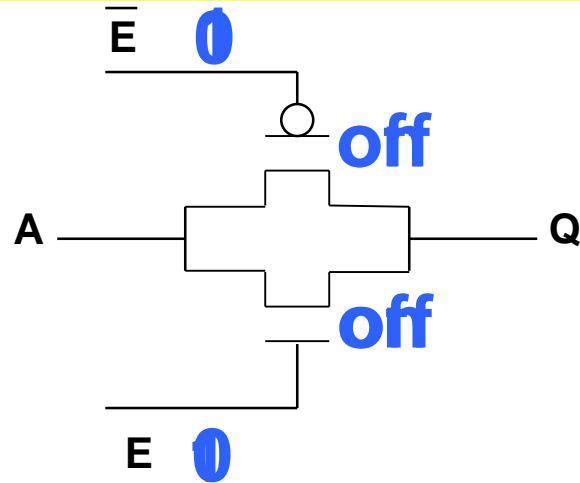
Three-state (Tri-state)

A CMOS-gate in addition to "1" or "0" is also provided with a third output state - the three-state "Z". (= unconnected output).

If many outputs are connected to the same line ("bus"), you can use one of the outputs at a time. The other outputs are held in the three-state condition.



Transmission gate (pass gate)



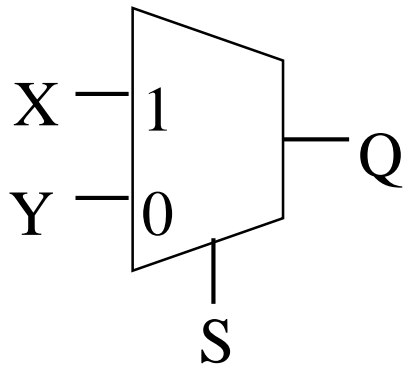
- The pass gate acts as a switch controlled by E
- If $E = 0$, the switch is open, $Q = Z$
- If $E = 1$, the switch is closed, $Q = A$
- Pass gates have a smaller driving capacity than ordinary gates

V_A	V_E	V_{OH}
L	L	Z
L	H	L
H	L	Z
H	H	H

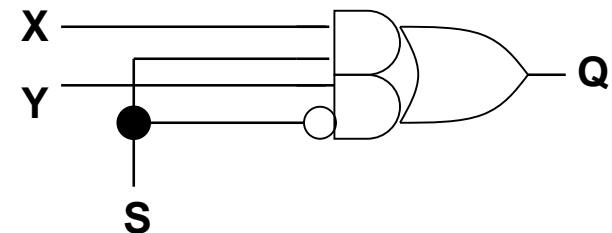
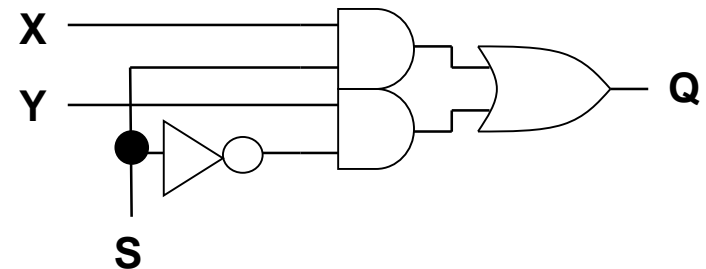
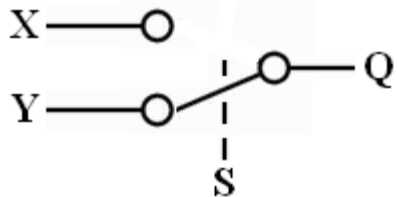
Area: $A_{TG} = 2$ Transistors

Multiplexer

Example: MUX is a data selector

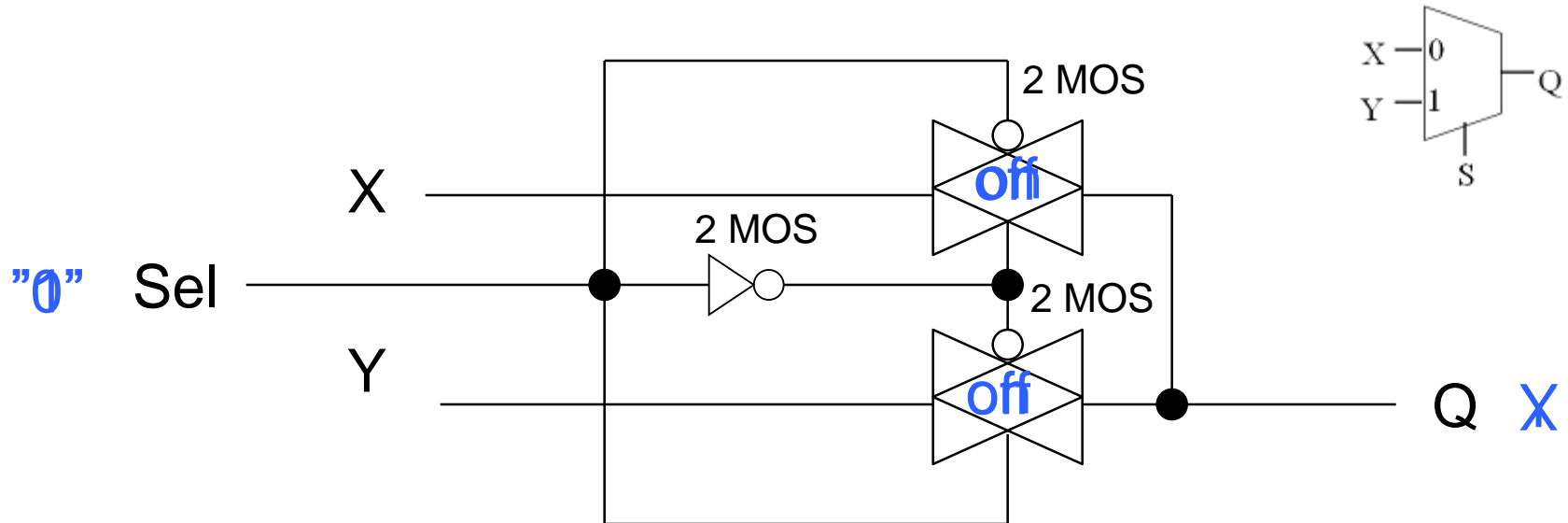


$$Q = XS + Y\bar{S}$$



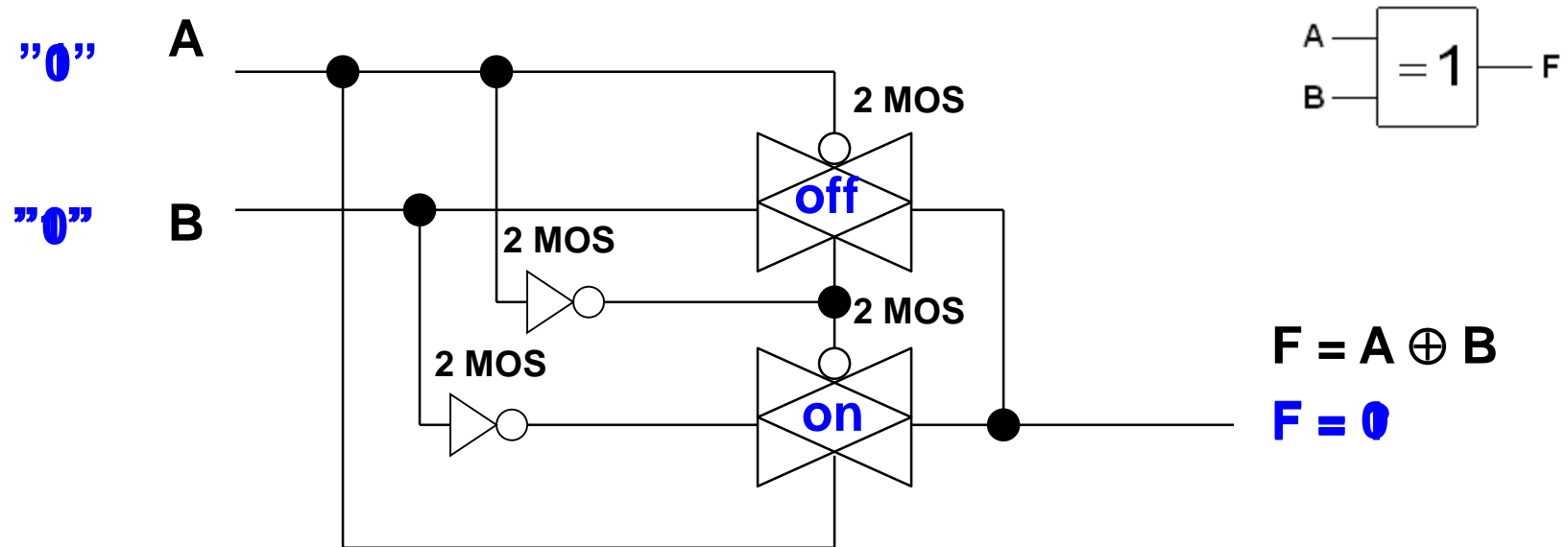
The inverter is denoted by a circle

MUX implementation by using Transmission gates



Area: $A_{\text{mux}} = 6$ Transistors

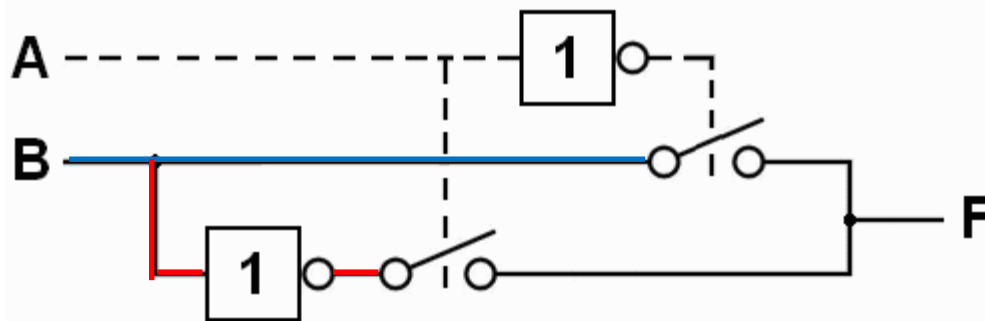
XOR implementation by using Transmission gates



Area: $A_{\text{mux}} = 8$ Transistors

*Hardly
obvious?*

XOR implementation by using Transmission gates



A	B	F
0	0	0
0	1	1
1	0	1
1	1	0

$F = B$

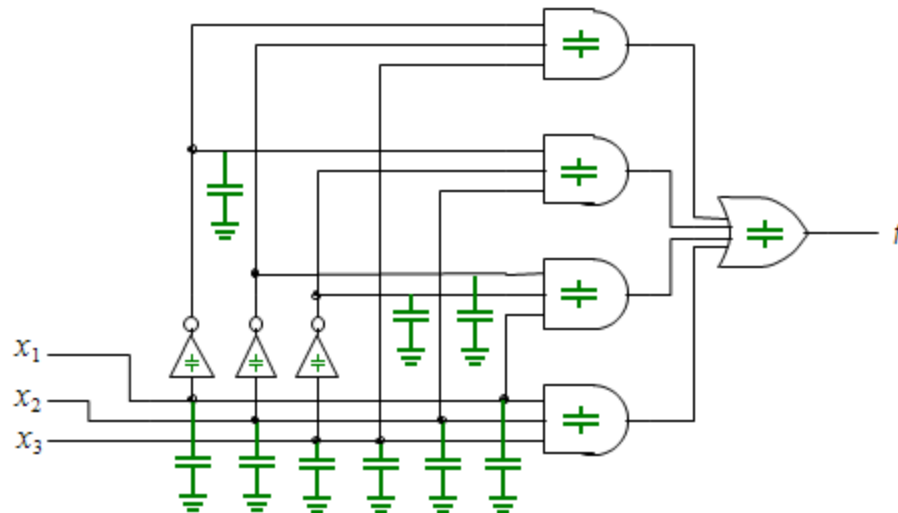
$F = \overline{B}$

Things Take Time ...

About delays in circuits

Delays in circuits

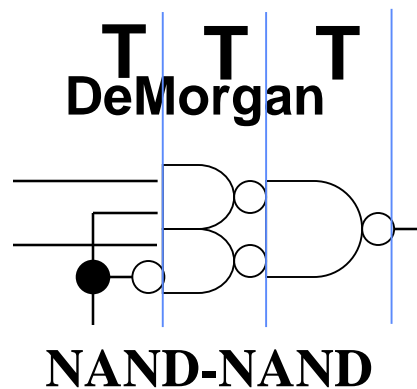
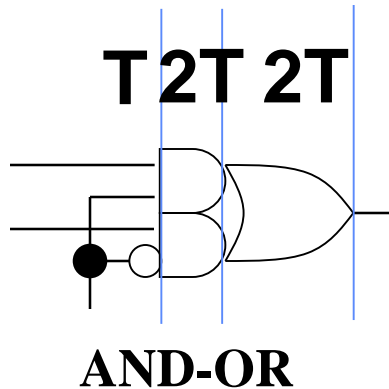
- Each wire in an electronic circuits has a capacitance
- Capacitance has a negative effect on the speed of operation of logic circuits



Typical delays

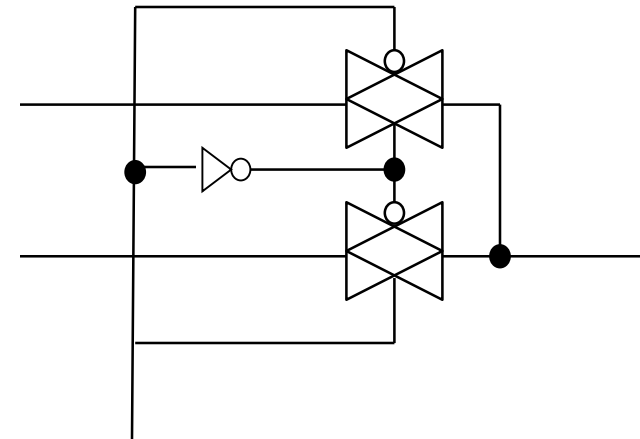
NAND, NOR	T
NOT	$\frac{1}{2} T$, T (if implemented using NAND-gate)
AND, OR	2T (2 NANDs in a row)
XOR, XNOR, MUX	3T...5T
XOR, MUX (using pass-gate)	2T

Optimized structures (MUX)



Area: $A_{MUX} = 2+6+6+6=20$
 Transistors
 Delay: $T_{MUX} = 5T_{NAND}$

Area: $A_{MUX} = 2+4+4+4 = 14$
 Transistors
 Delay: $T_{MUX} = 3T_{NAND}$

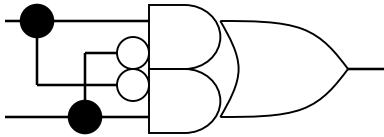


Area: $A_{MUX} = 6$ Transistors
 Delay: $T_{MUX} = \sim 2T_{NAND}$



Best!

Optimized structures (XOR)

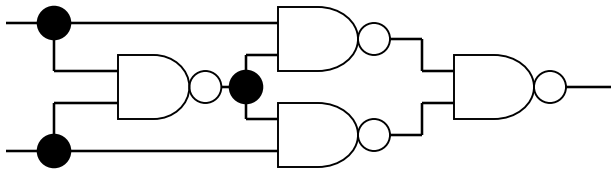


Area: $A_{MUX} = 2+2+6+6+6=22$

Transistors

Delay: $T_{MUX} = 5T_{NAND}$

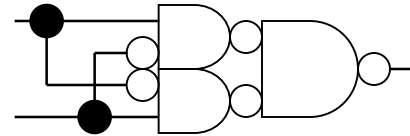
NAND only



Area: $A_{MUX} = 16$ Transistors

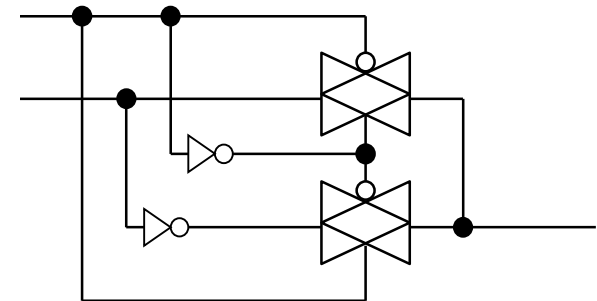
Delay: $T_{MUX} = 3T_{NAND}$

DeMorgan



Area: $A_{MUX} = 2+2+4+4+4=16$ Transistors

Delay: $T_{MUX} = 3T_{NAND}$



Area: $A_{MUX} = 2 \times 4 = 8$ Transistors

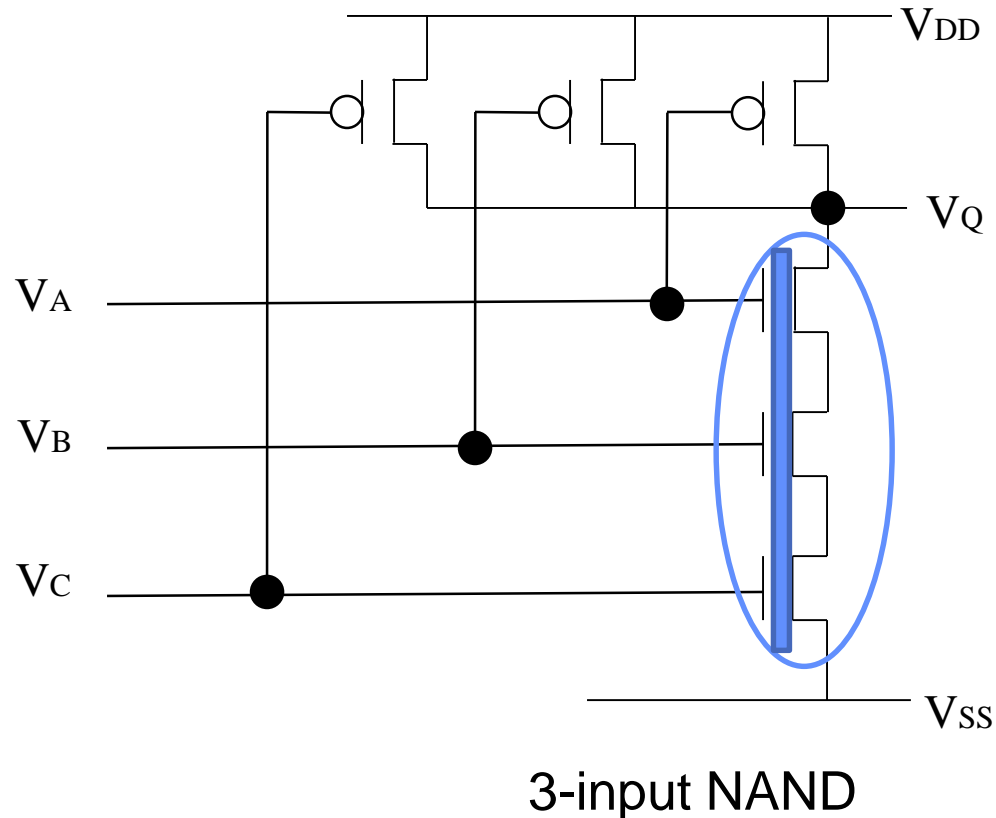
Delay: $T_{MUX} = \sim 2T_{NAND}$

 **Best!**

Fan-in

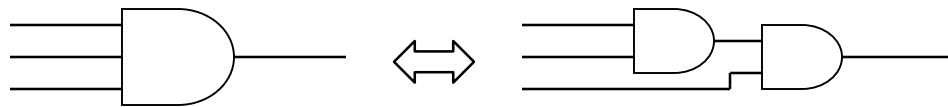
- **Fan-in** is the number of inputs to the gate.
- If a gate has many inputs, it has a larger internal capacitance \Rightarrow its internal delay T_i (also called the intrinsic delay) becomes larger.

Gates with more than 2 inputs

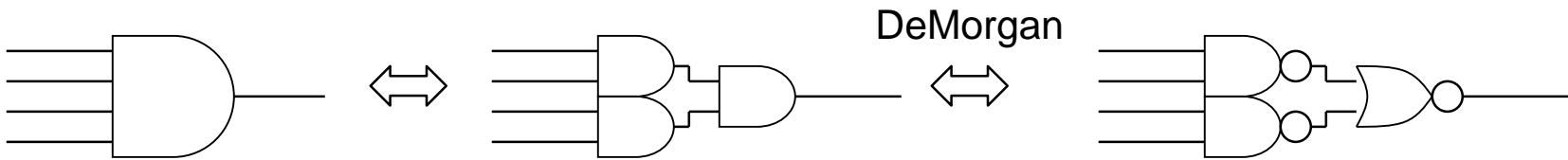


- Gates with more than three or four inputs are used rarely
- The internal capacitance becomes too large and gates too slow
- A long line of transistors connected in series gives long delay!

High fan-in is solved with tree-structures



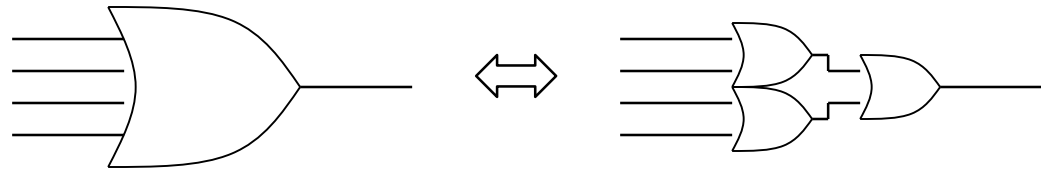
$$a \cdot b \cdot c = a \cdot (b \cdot c)$$



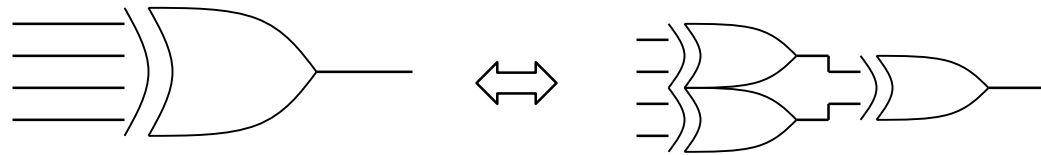
$$a \cdot b \cdot c \cdot d = (a \cdot b) \cdot (c \cdot d)$$

$$\overline{\overline{(a \cdot b)} + \overline{\overline{(c \cdot d)}}} = a \cdot b \cdot c \cdot d$$

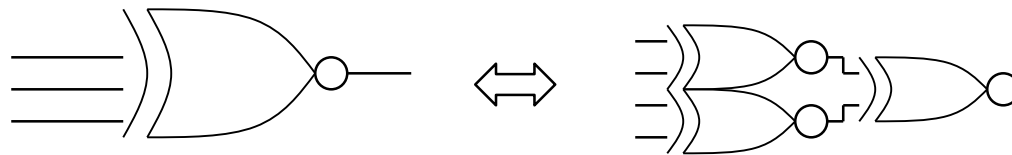
More tree structures ...



$$a + b + c + d = (a + b) + (c + d)$$



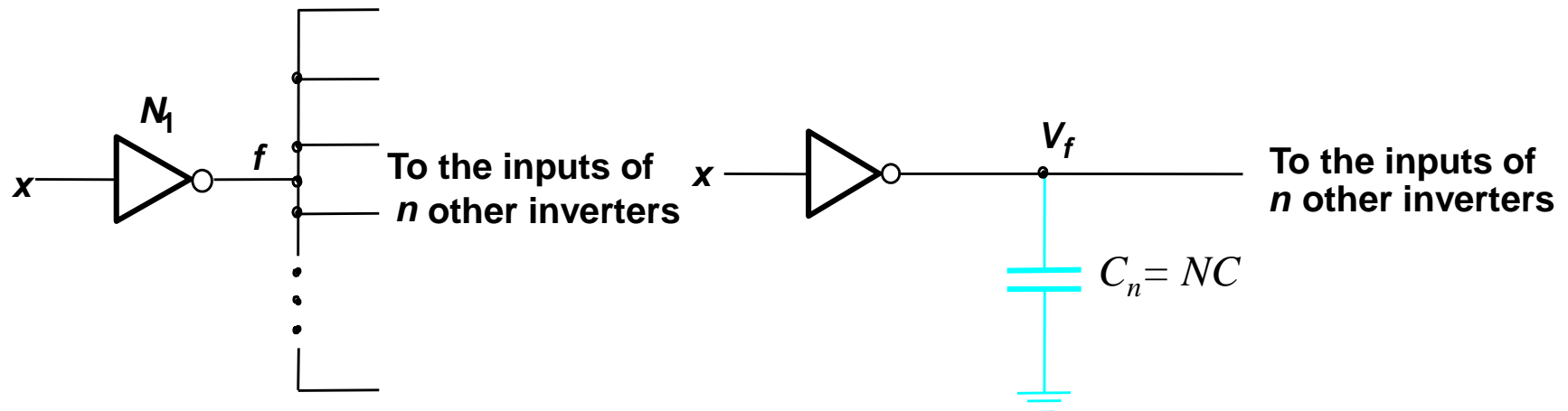
$$a \oplus b \oplus c \oplus d = (a \oplus b) \oplus (c \oplus d)$$



$$\overline{a \oplus b \oplus c \oplus d} = \overline{\overline{(a \oplus b) \oplus (c \oplus d)}}$$

Fan-out

- **Fan-out** is the number of other gates that a specific gate drives
- Each of the driven gates increases the capacitive load on f

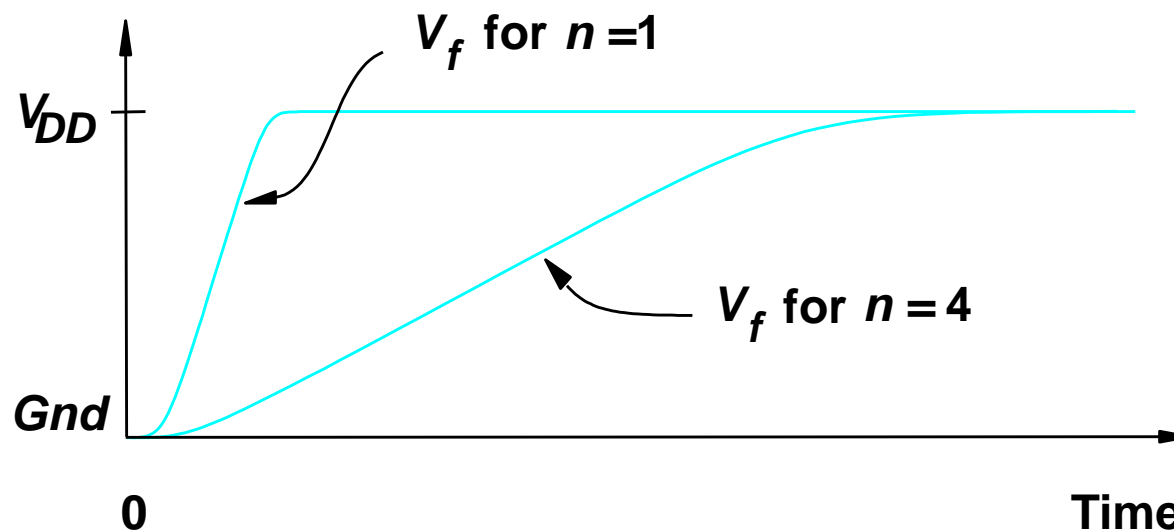


(A) Inverter that drives n other inverters

(B) Equivalent circuit for timing purposes

Effect of fan-out on propagation delay

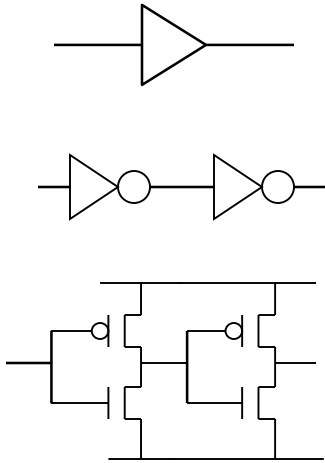
- The propagation time for different fan-outs



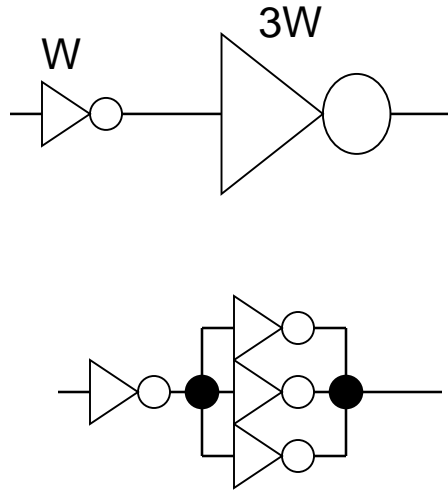
Buffering

- A buffer is a circuit that implements the function $f(x) = x$
- They have larger transistors and can drive higher-than-normal capacitive loads
- They are also used when high current flow is needed to drive external devices

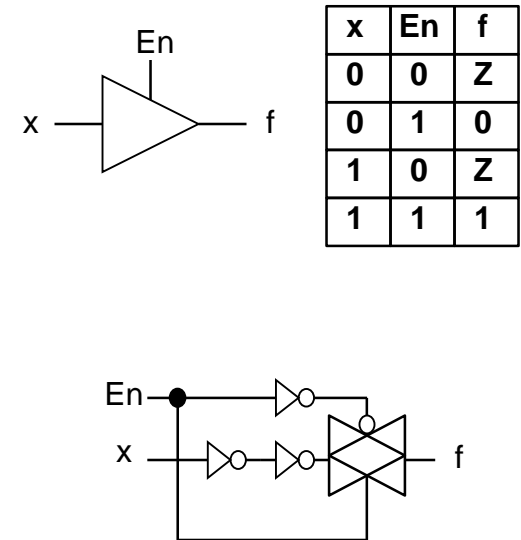
High Fan-out: Use Buffers



Non-Inverting Buffer



High-Fan-Out Buffer



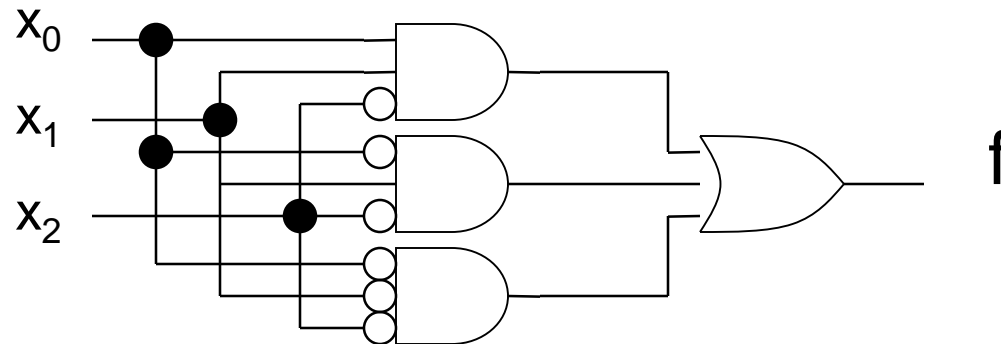
Tri-State Buffer

When $En = 0$, f is disconnected from x

When $En = 1$, $f = x$

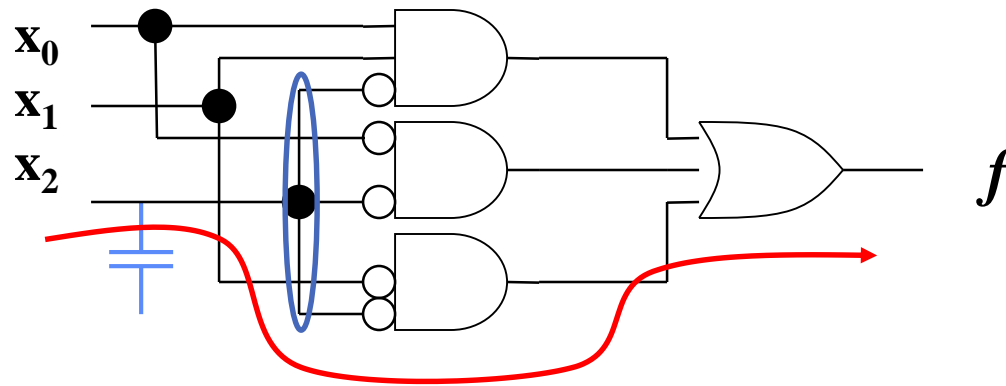
Critical Path (Longest path)

$$f = \sum m(3,2,0) = \bar{x}_2 x_1 x_0 + \bar{x}_2 x_1 \bar{x}_0 + \bar{x}_2 \bar{x}_1 \bar{x}_0$$



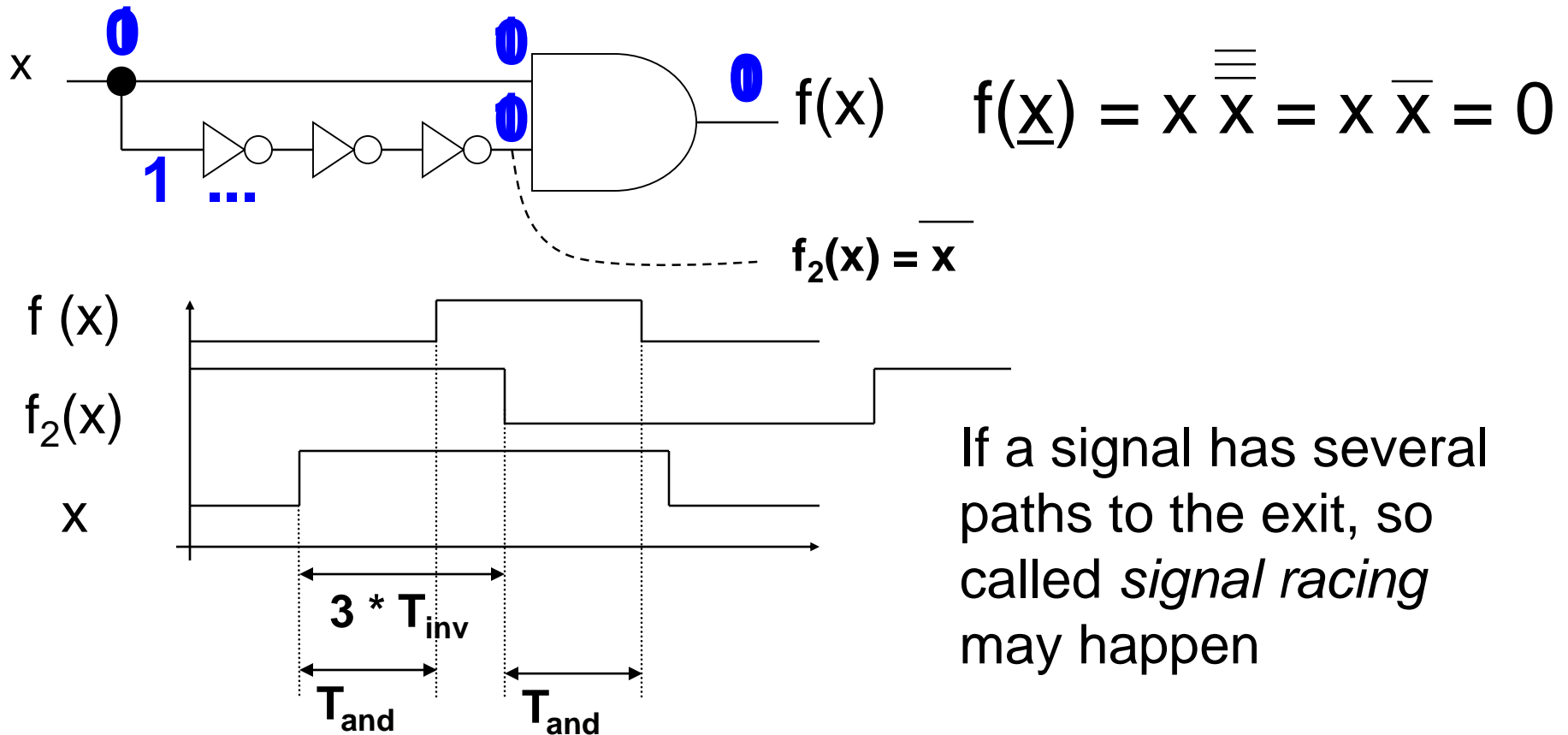
Critical Path (cont'd.)

$$f = x_0 x_1 \bar{x}_2 + \bar{x}_0 \bar{x}_2 + \bar{x}_1 \bar{x}_2$$



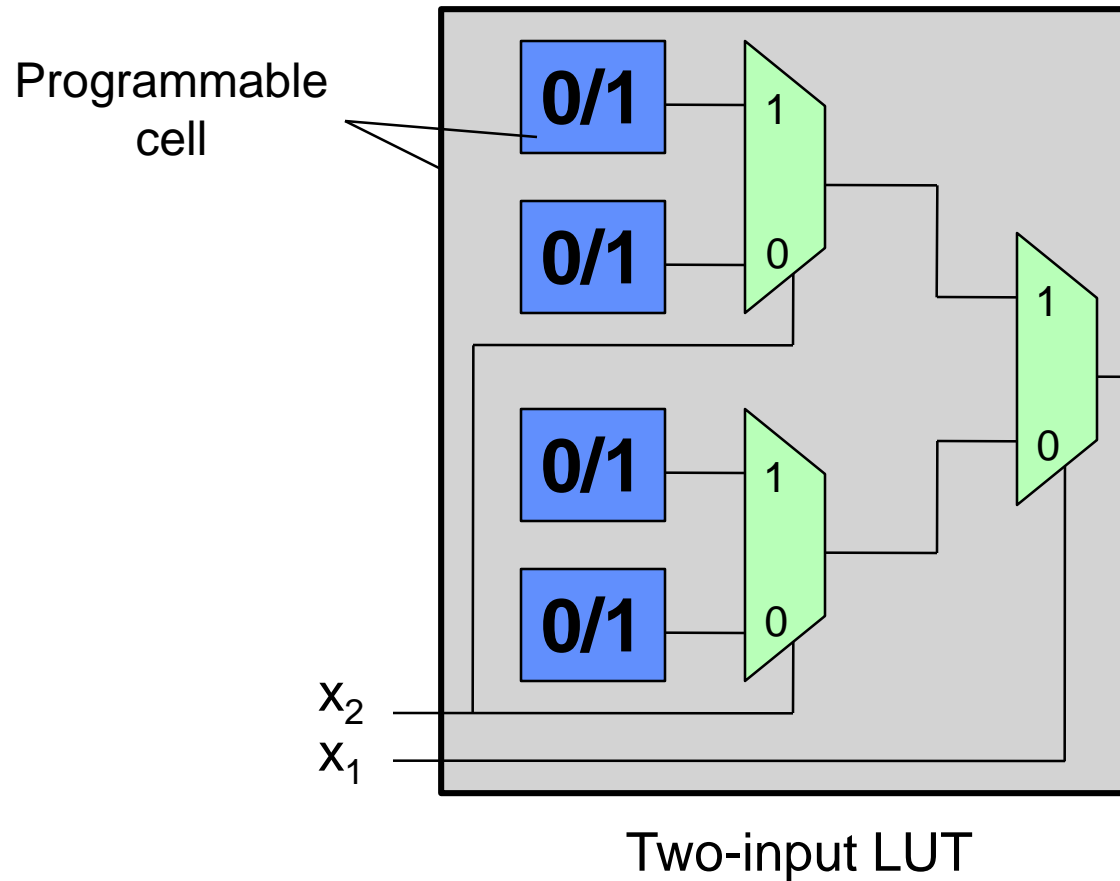
$x_0 x_1 x_2$ all pass NOT , AND, and OR on their way to the output f , but x_2 has the load of *three* inputs (it is two for x_0 and x_1). Thus "Critical path" becomes from x_2 to f !

Signal Racing



If a signal has several paths to the exit, so called *signal racing* may happen

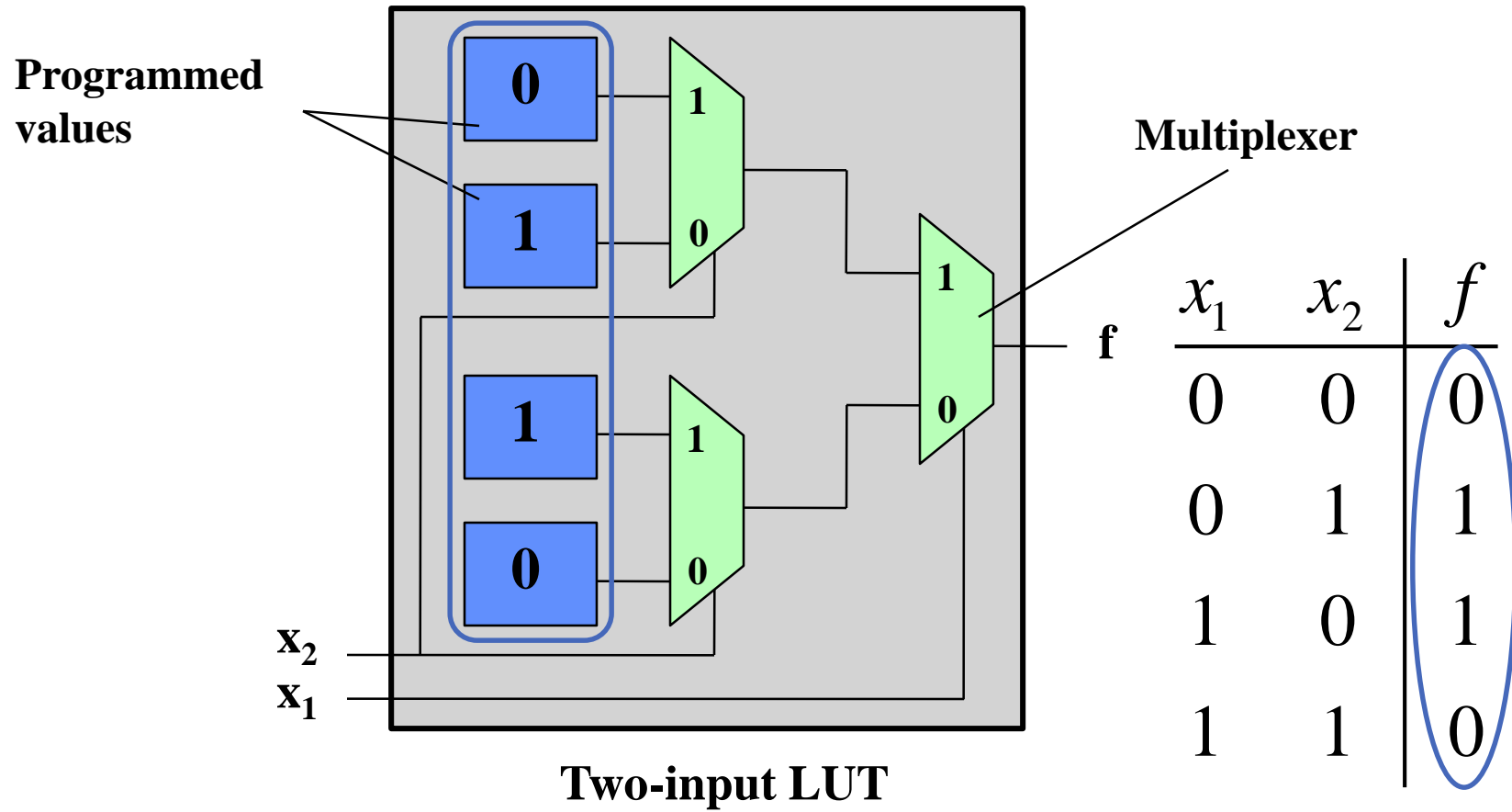
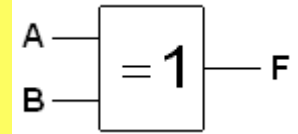
Look-up tables (LUT)



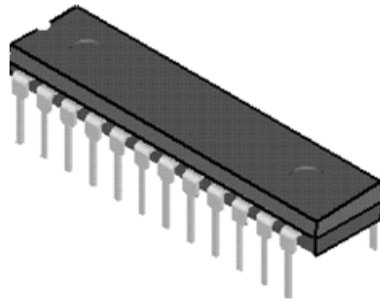
A LUT with n inputs can realize all combinational functions with up to n inputs

The usual size in an FPGA is $n = 4$

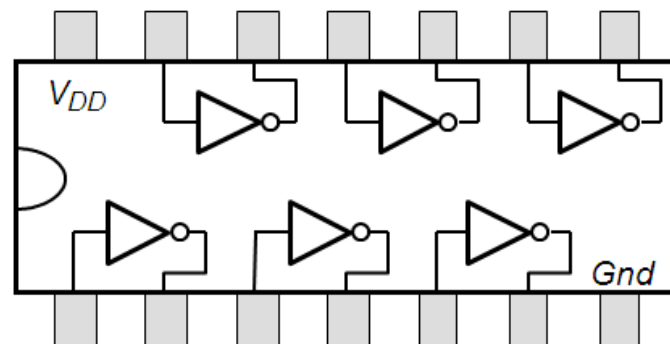
Example: XOR gate



7400 Series Standard Chips

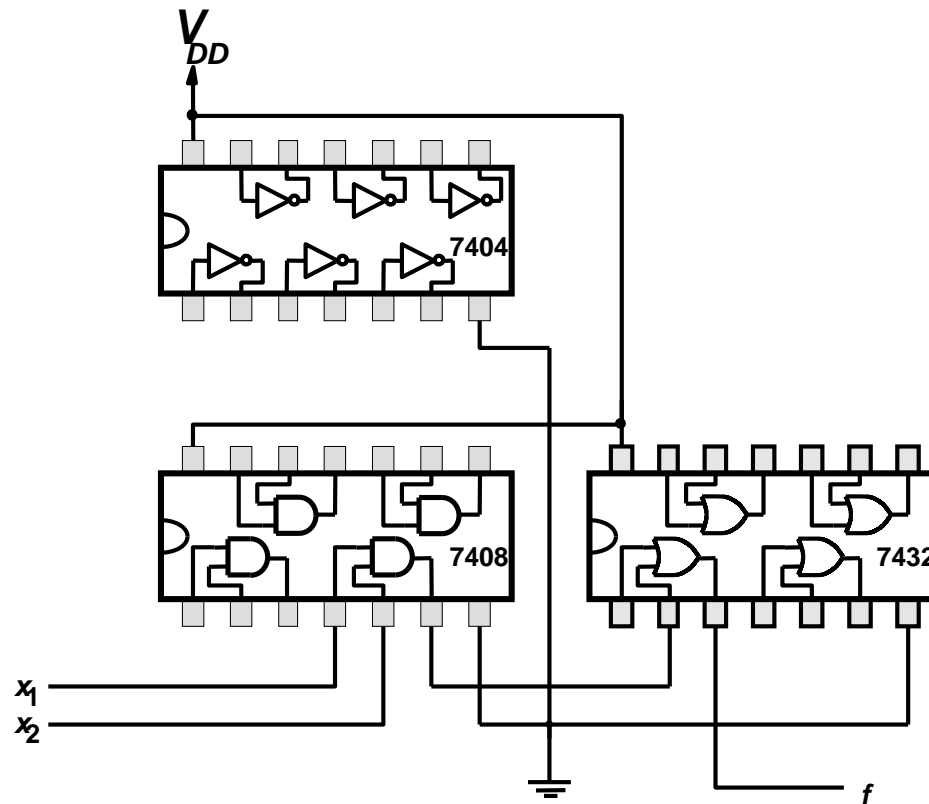


(a) Dual-inline package



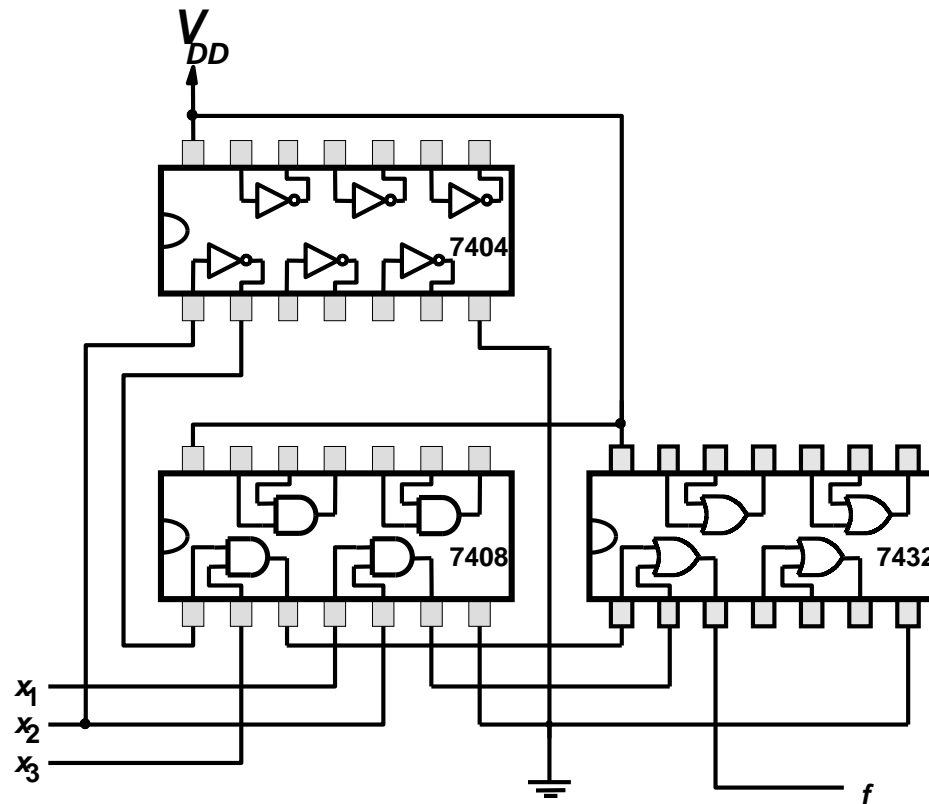
(b) Structure of 7404 chip

Implementation of a logic function



An implementation of $f = x_1x_2 + x_2\bar{x}_3$

Implementation of a logic function

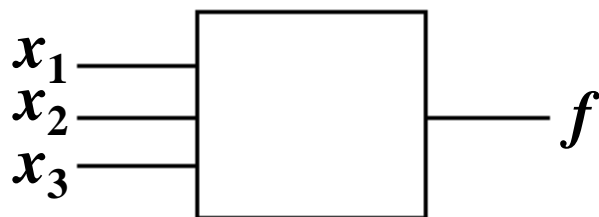


An implementation of $f = x_1x_2 + \bar{x}_2x_3$

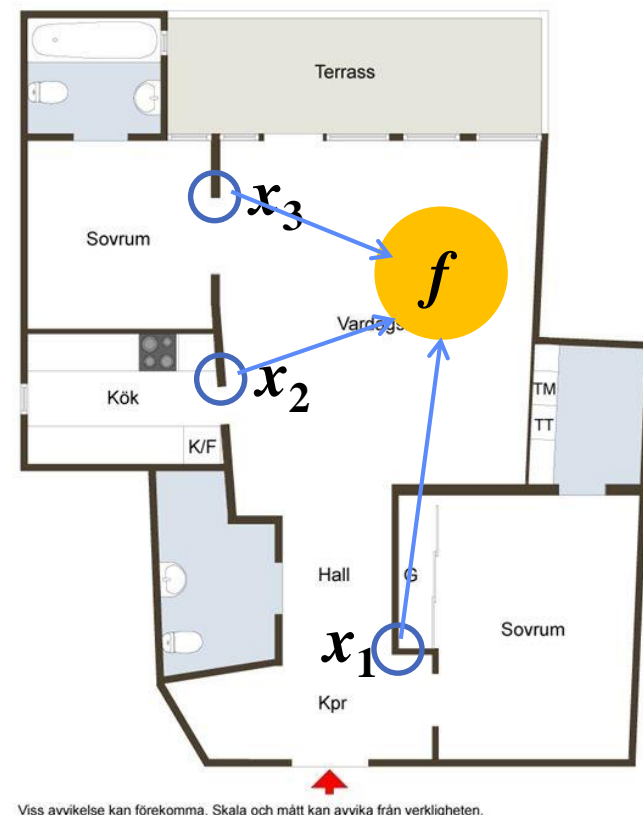
Three-way light control

Brown/Vranesic: 2.8.1

Suppose that we need to be able to turn on / off the lamp from three different places.

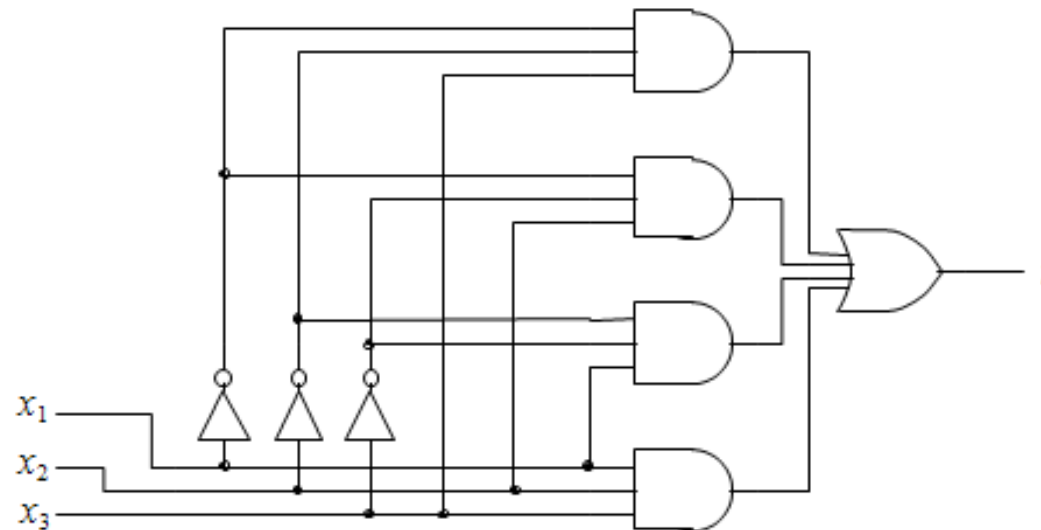


x_1	x_2	x_3	f
0	0	0	0
0	0	1	1
0	1	0	1
0	1	1	0
1	0	0	1
1	0	1	0
1	1	0	0
1	1	1	1



Three-way light control

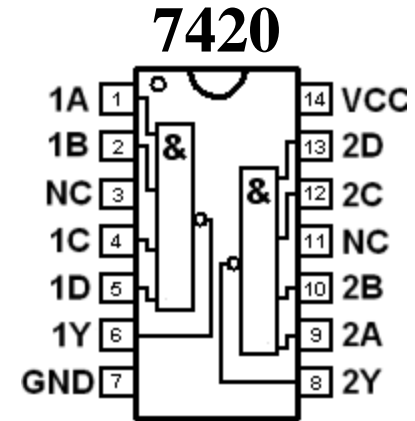
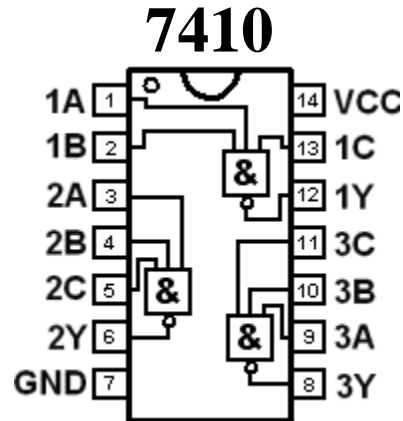
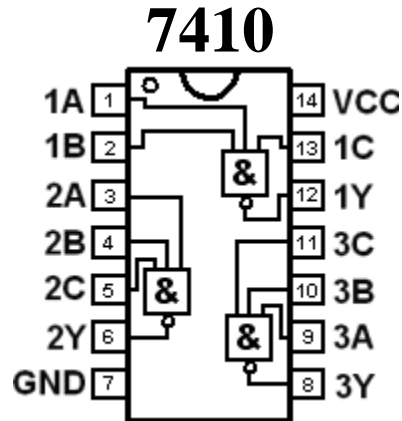
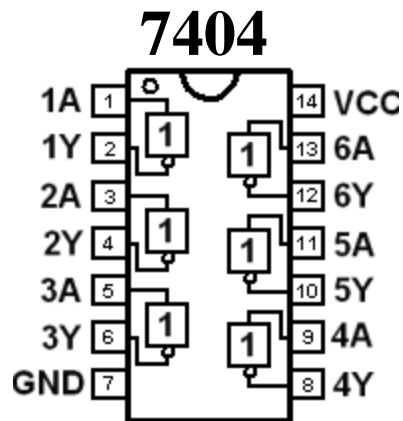
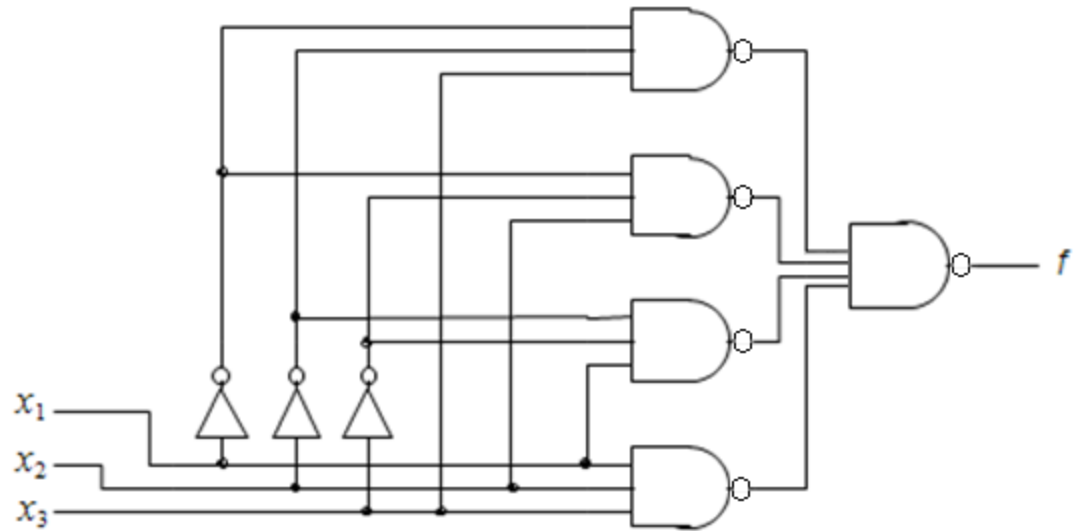
$$f = \sum m(1,2,4,7) = \bar{x}_1\bar{x}_2x_3 + \bar{x}_1x_2\bar{x}_3 + x_1\bar{x}_2\bar{x}_3 + x_1x_2x_3$$



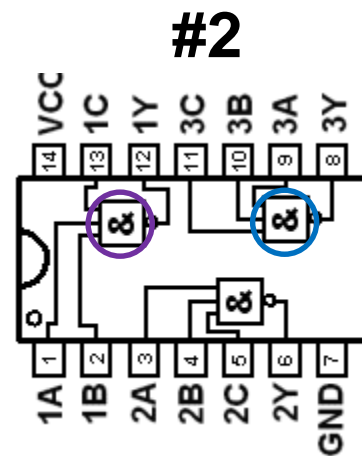
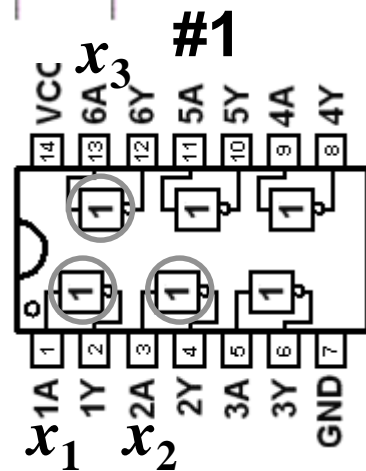
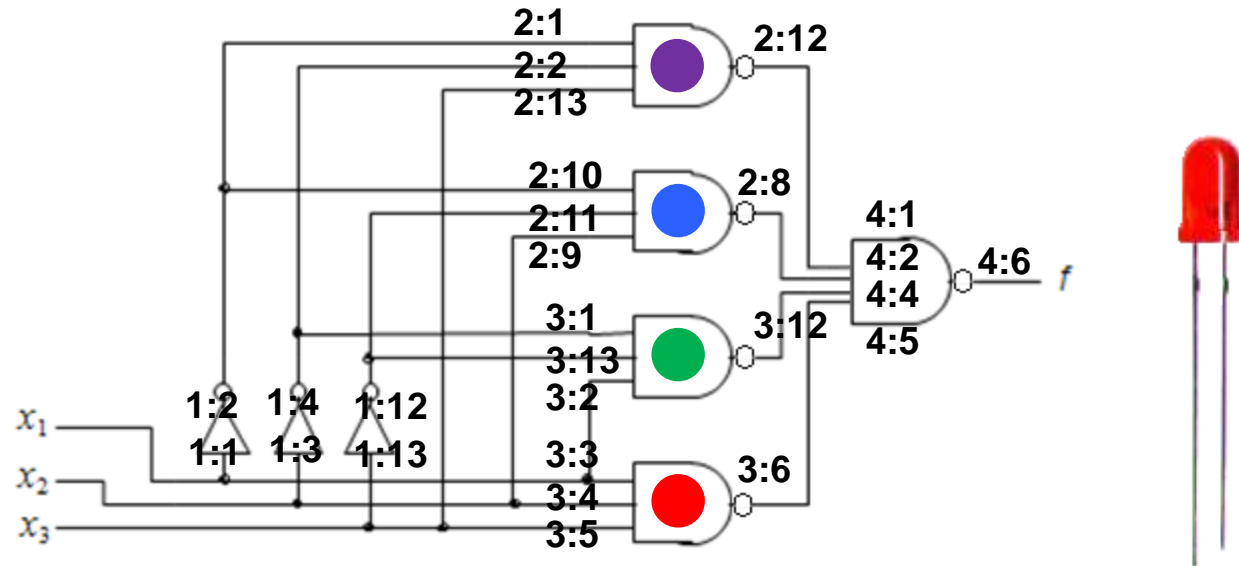
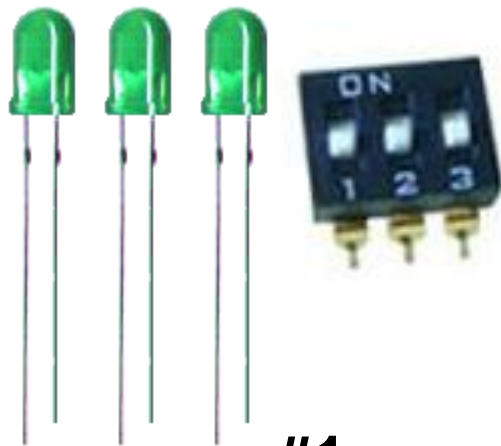
(a) Sum-of-products realization

NAND-NAND

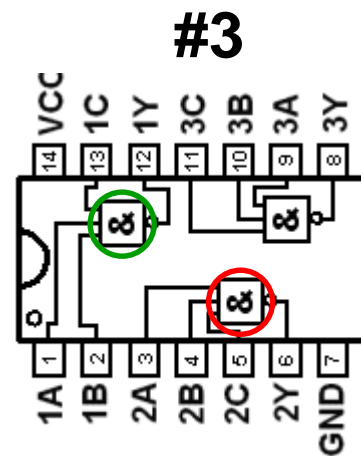
If we change to
NAND-NAND all
necessary gates are
included with the
simulator.



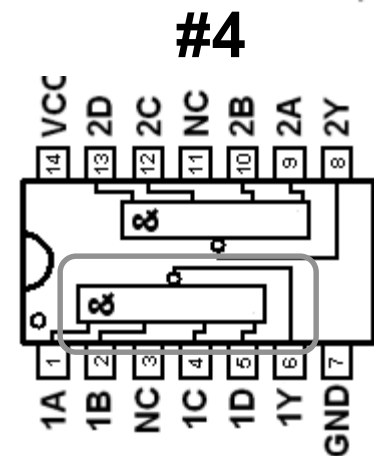
You must enter the pin number in the schematic - otherwise you can get lost!



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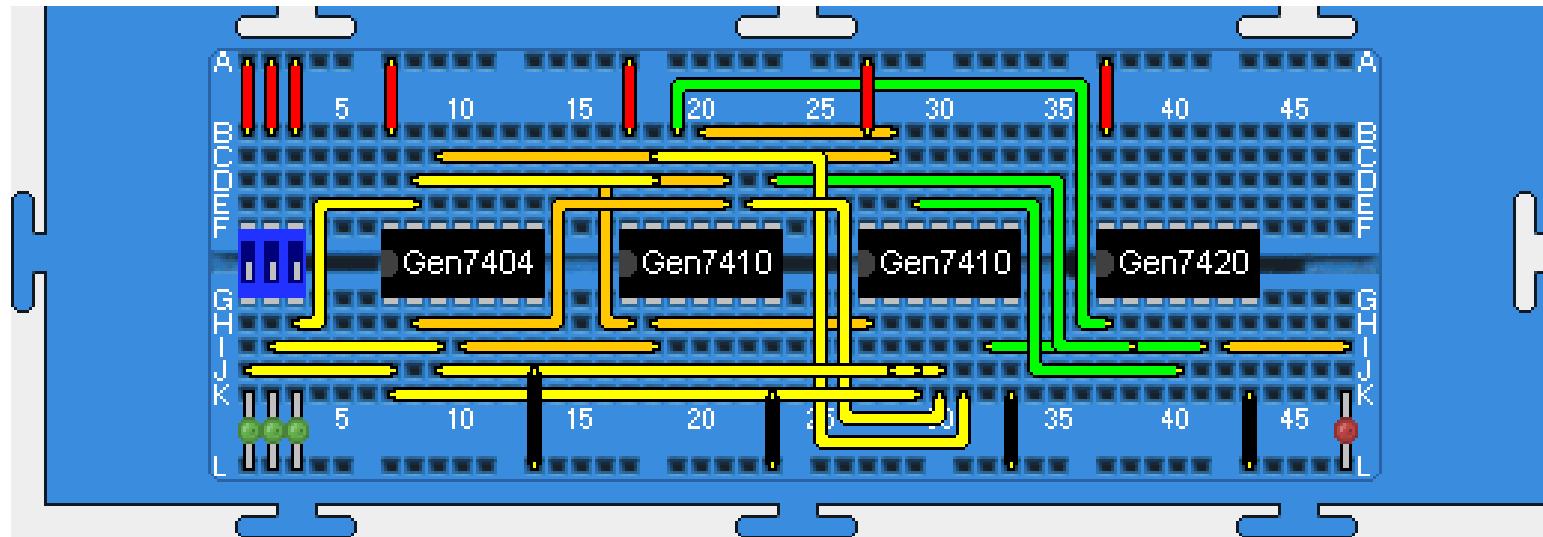


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Simulate!



Summary

- Logic gates can be implemented with CMOS technology
- Logic circuits have a delay
- CMOS circuits have relatively low power consumption

